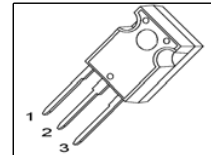


**Cool MOS™ Power Transistor**
**Feature**

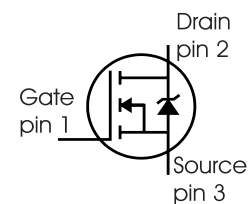
- New revolutionary high voltage technology
- Worldwide best  $R_{DS(on)}$  in TO 247
- Ultra low gate charge
- Periodic avalanche rated
- Extreme  $dv/dt$  rated
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>0)</sup> for target applications

$V_{DS}$	800	V
$R_{DS(on)}$	0.29	$\Omega$
$I_D$	17	A

PG-TO247



Type	Package	Ordering Code	Marking
SPW17N80C3	PG-TO247	Q67040-S4359	17N80C3


**Maximum Ratings**

Parameter	Symbol	Value	Unit
Continuous drain current	$I_D$		A
$T_C = 25\text{ }^\circ\text{C}$		17	
$T_C = 100\text{ }^\circ\text{C}$		11	
Pulsed drain current, $t_p$ limited by $T_{jmax}$	$I_{D\text{ puls}}$	51	
Avalanche energy, single pulse	$E_{AS}$	670	mJ
$I_D = 3.4\text{ A}$ , $V_{DD} = 50\text{ V}$			
Avalanche energy, repetitive $t_{AR}$ limited by $T_{jmax}$ <sup>1)</sup>	$E_{AR}$	0.5	
$I_D = 17\text{ A}$ , $V_{DD} = 50\text{ V}$			
Avalanche current, repetitive $t_{AR}$ limited by $T_{jmax}$	$I_{AR}$	17	A
Gate source voltage	$V_{GS}$	$\pm 20$	V
Gate source voltage AC ( $f > 1\text{ Hz}$ )	$V_{GS}$	$\pm 30$	
Power dissipation, $T_C = 25\text{ }^\circ\text{C}$	$P_{tot}$	208	W
Operating and storage temperature	$T_j, T_{stg}$	-55... +150	$^\circ\text{C}$

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Drain Source voltage slope $V_{DS} = 640 \text{ V}$ , $I_D = 17 \text{ A}$ , $T_j = 125 \text{ }^\circ\text{C}$	$dv/dt$	50	V/ns

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	$R_{thJC}$	-	-	0.6	K/W
Thermal resistance, junction - ambient, leaded	$R_{thJA}$	-	-	62	
Soldering temperature, wavesoldering 1.6 mm (0.063 in.) from case for 10s	$T_{sold}$	-	-	260	$^\circ\text{C}$

**Electrical Characteristics, at  $T_j=25^\circ\text{C}$  unless otherwise specified**

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{V}$ , $I_D=0.25\text{mA}$	800	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{V}$ , $I_D=17\text{A}$	-	870	-	
Gate threshold voltage	$V_{GS(th)}$	$I_D=1000\mu\text{A}$ , $V_{GS}=V_{DS}$	2.1	3	3.9	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=800\text{V}$ , $V_{GS}=0\text{V}$ , $T_j=25^\circ\text{C}$ , $T_j=150^\circ\text{C}$	- -	0.5 -	25 250	$\mu\text{A}$
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{V}$ , $V_{DS}=0\text{V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$ , $I_D=11\text{A}$ , $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	- -	0.25 0.78	0.29 -	$\Omega$
Gate input resistance	$R_G$	$f=1\text{MHz}$ , open Drain	-	0.7	-	

**Electrical Characteristics** , at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Transconductance	$g_{fs}$	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = 11\text{A}$	-	15	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$	-	2320	-	pF
Output capacitance	$C_{oss}$		-	1250	-	
Reverse transfer capacitance	$C_{rss}$		-	60	-	
Effective output capacitance, <sup>2)</sup> energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 0\text{V to } 480\text{V}$	-	59	-	pF
Effective output capacitance, <sup>3)</sup> time related	$C_{o(tr)}$		-	124	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 400\text{V}$ , $V_{GS} = 0/10\text{V}$ , $I_D = 17\text{A}$ , $R_G = 4.7\Omega$ , $T_j = 125\text{ }^\circ\text{C}$	-	25	-	ns
Rise time	$t_r$		-	15	-	
Turn-off delay time	$t_{d(off)}$		-	72	82	
Fall time	$t_f$		-	6	9	

**Gate Charge Characteristics**

Gate to source charge	$Q_{gs}$	$V_{DD} = 640\text{V}$ , $I_D = 17\text{A}$	-	12	-	nC
Gate to drain charge	$Q_{gd}$		-	46	-	
Gate charge total	$Q_g$	$V_{DD} = 640\text{V}$ , $I_D = 17\text{A}$ , $V_{GS} = 0\text{ to } 10\text{V}$	-	91	177	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 640\text{V}$ , $I_D = 17\text{A}$	-	6	-	V

<sup>0</sup>J-STD20 and JESD22

<sup>1</sup>Repetitive avalanche causes additional power losses that can be calculated as  $P_{AV} = E_{AR} \cdot f$ .

<sup>2</sup> $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

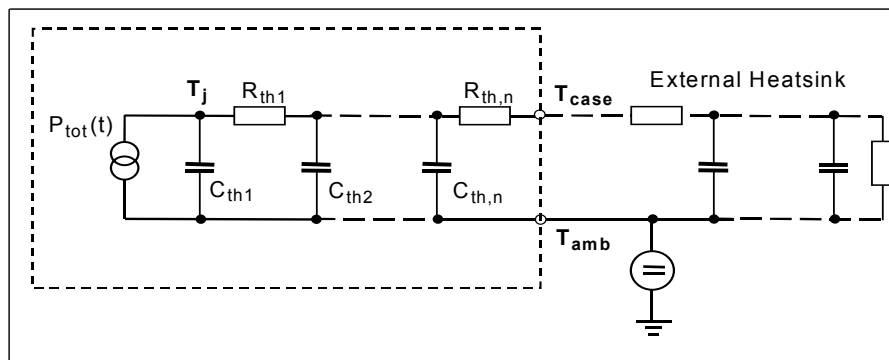
<sup>3</sup> $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

**Electrical Characteristics, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	$I_S$	$T_C=25^\circ\text{C}$	-	-	17	A
Inverse diode direct current, pulsed	$I_{SM}$		-	-	51	
Inverse diode forward voltage	$V_{SD}$	$V_{GS}=0\text{V}, I_F=I_S$	-	1	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=400\text{V}, I_F=I_S,$	-	550	-	ns
Reverse recovery charge	$Q_{rr}$	$di_F/dt=100\text{A}/\mu\text{s}$	-	15	-	$\mu\text{C}$
Peak reverse recovery current	$I_{rrm}$		-	51	-	A
Peak rate of fall of reverse recovery current	$di_{rr}/dt$		-	1200	-	$\text{A}/\mu\text{s}$

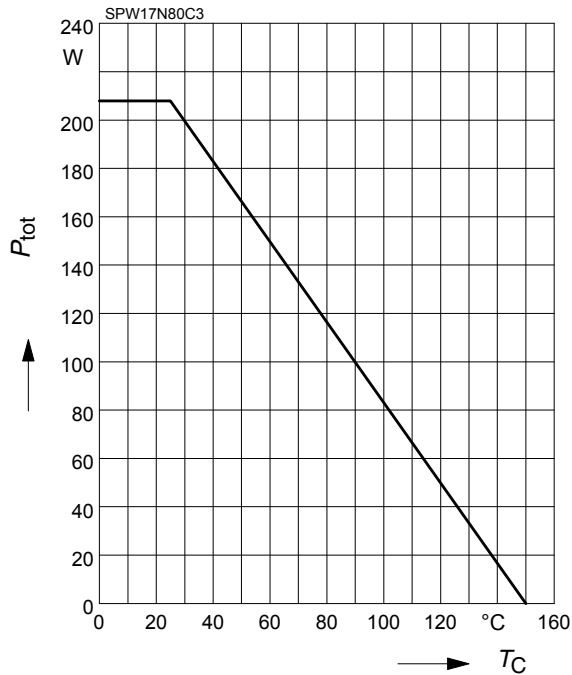
**Typical Transient Thermal Characteristics**

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
$R_{th1}$	0.00812	K/W	$C_{th1}$	0.0003562	Ws/K
$R_{th2}$	0.016		$C_{th2}$	0.001337	
$R_{th3}$	0.031		$C_{th3}$	0.001831	
$R_{th4}$	0.114		$C_{th4}$	0.005033	
$R_{th5}$	0.135		$C_{th5}$	0.012	
$R_{th6}$	0.059		$C_{th6}$	0.092	



### 1 Power dissipation

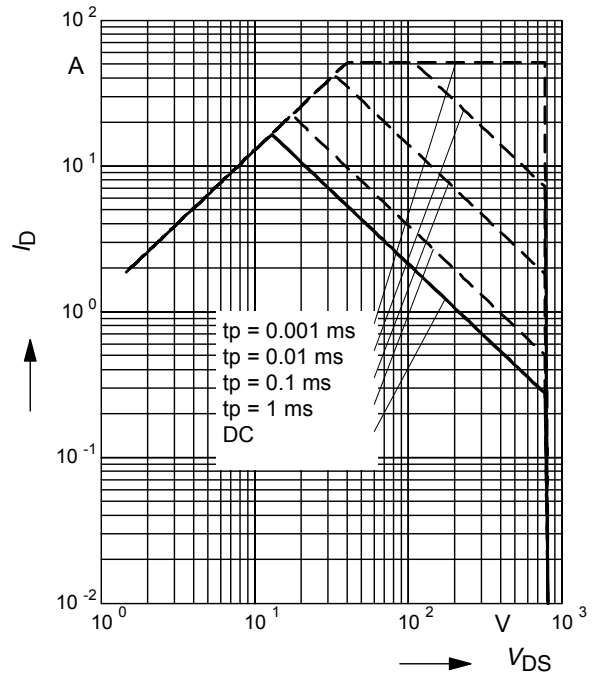
$$P_{tot} = f(T_C)$$



### 2 Safe operating area

$$I_D = f(V_{DS})$$

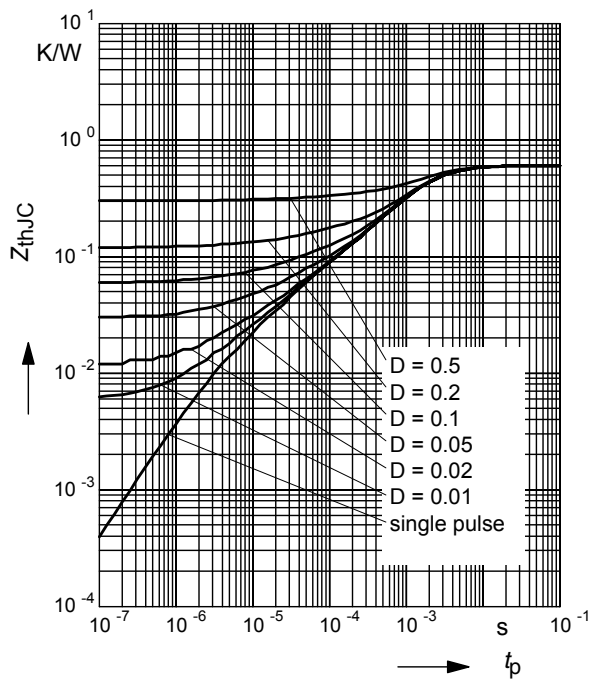
parameter :  $D = 0$  ,  $T_C = 25^\circ\text{C}$



### 3 Transient thermal impedance

$$Z_{thJC} = f(t_p)$$

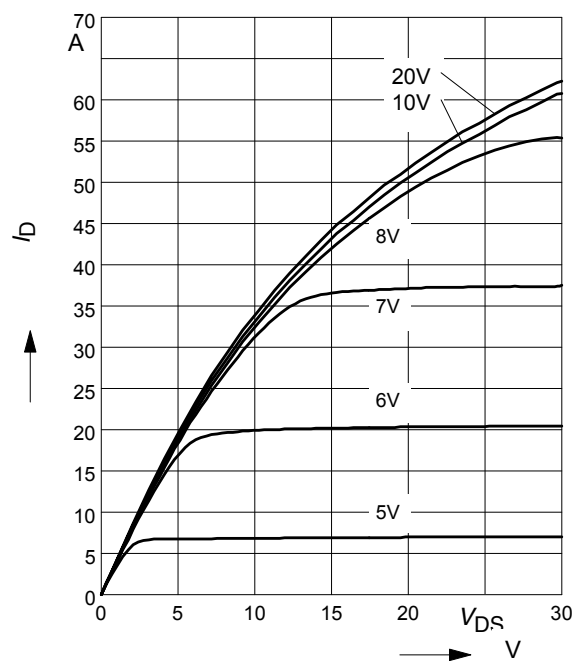
parameter:  $D = t_p/T$



### 4 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

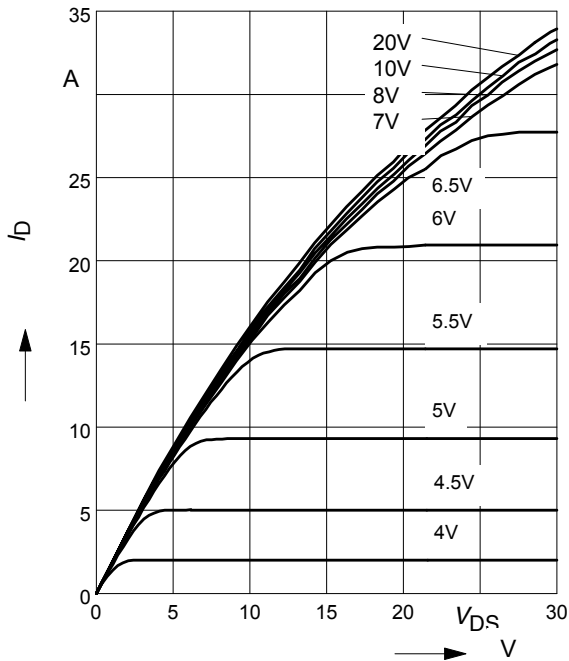
parameter:  $t_p = 10 \mu\text{s}$ ,  $V_{GS}$



**5 Typ. output characteristic**

$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$

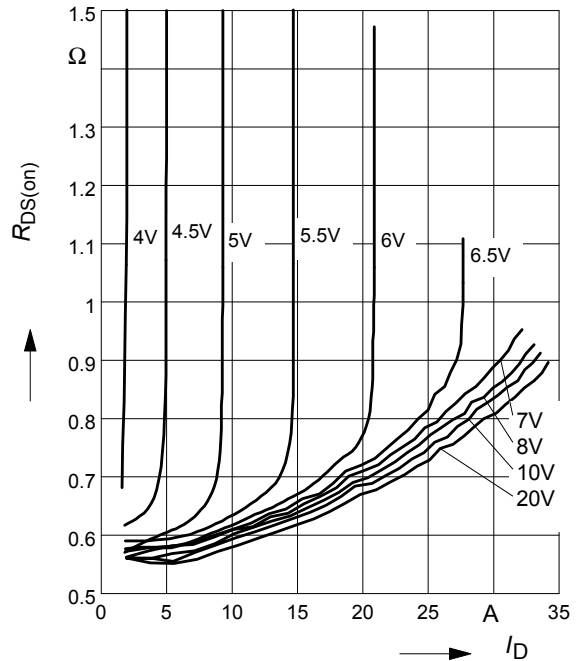
parameter:  $t_p = 10 \mu\text{s}, V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D)$

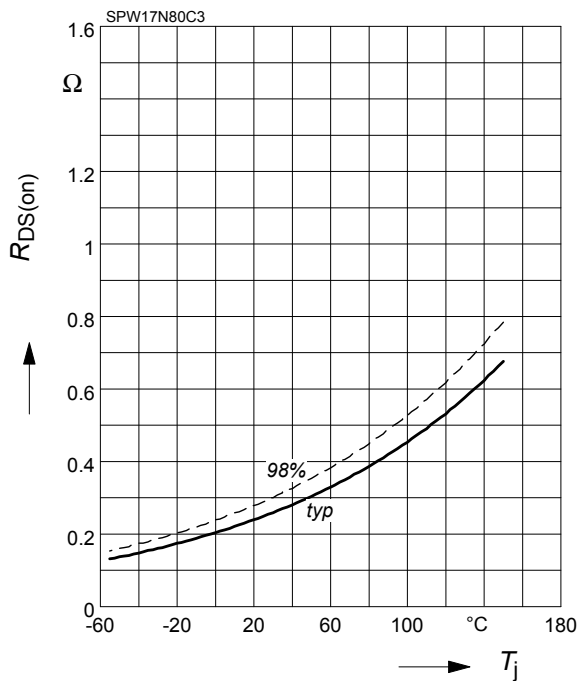
parameter:  $T_j = 150^\circ\text{C}, V_{GS}$



**7 Drain-source on-state resistance**

$R_{DS(on)} = f(T_j)$

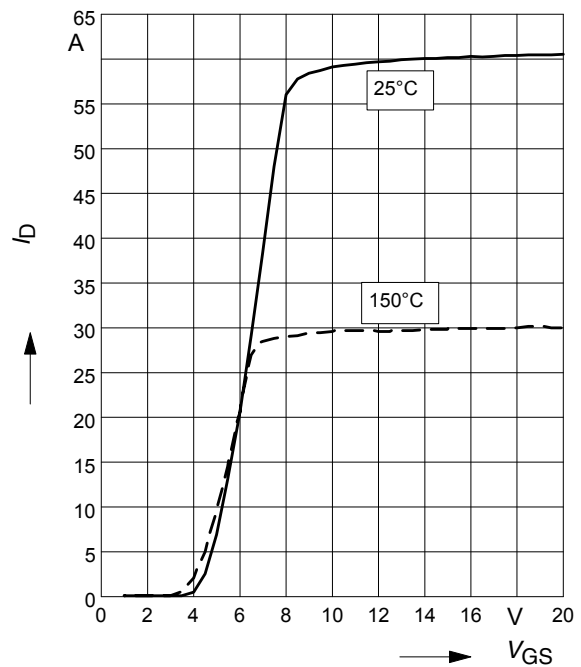
parameter:  $I_D = 11 \text{ A}, V_{GS} = 10 \text{ V}$



**8 Typ. transfer characteristics**

$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

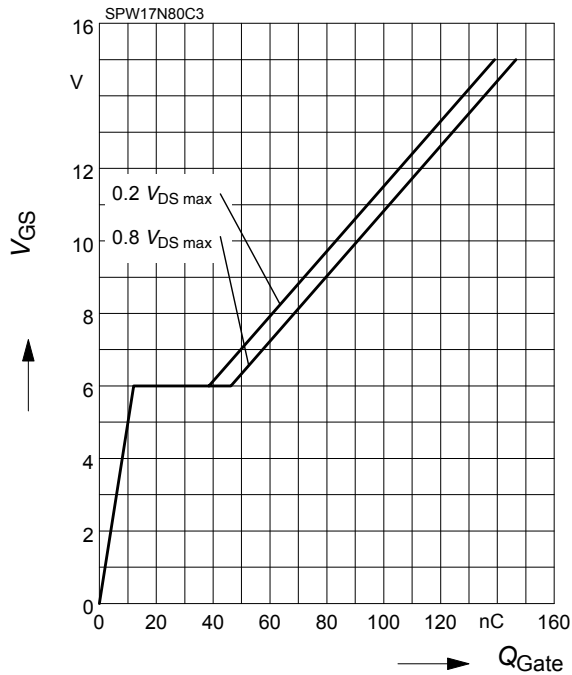
parameter:  $t_p = 10 \mu\text{s}$



**9 Typ. gate charge**

$$V_{GS} = f(Q_{Gate})$$

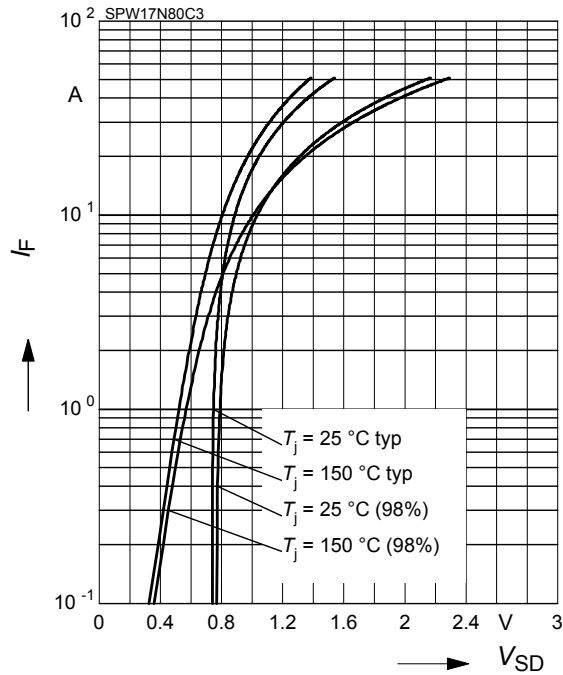
parameter:  $I_D = 17\text{ A}$  pulsed



**10 Forward characteristics of body diode**

$$I_F = f(V_{SD})$$

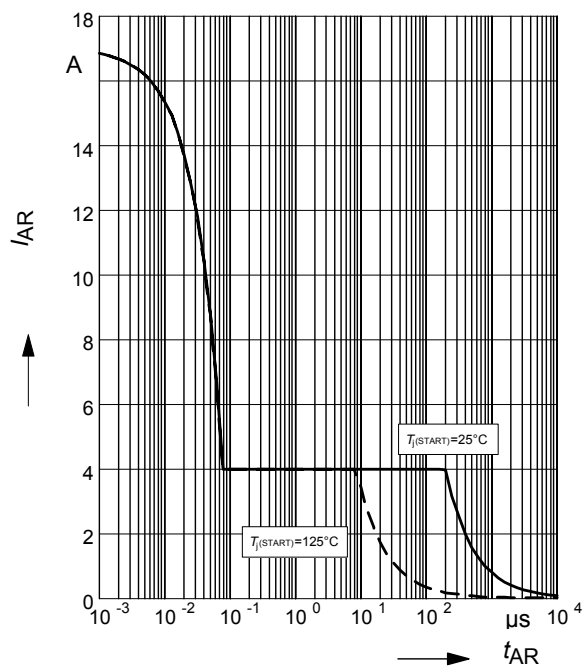
parameter:  $T_j, t_p = 10\ \mu\text{s}$



**11 Avalanche SOA**

$$I_{AR} = f(t_{AR})$$

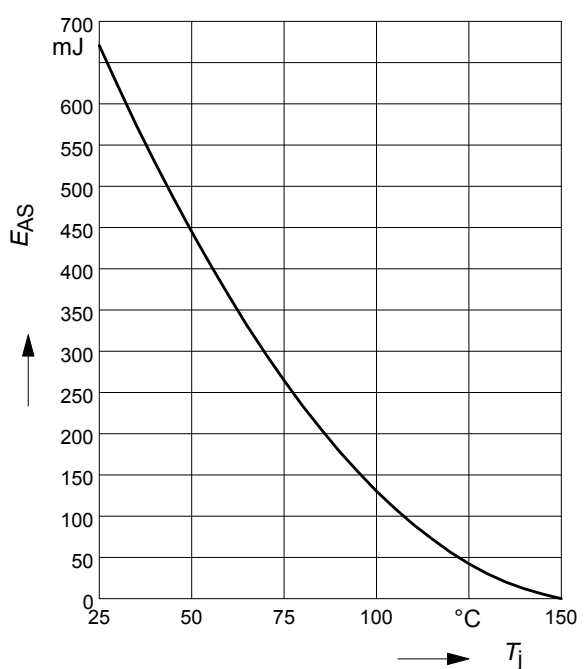
par.:  $T_j \leq 150\ \text{°C}$



**12 Avalanche energy**

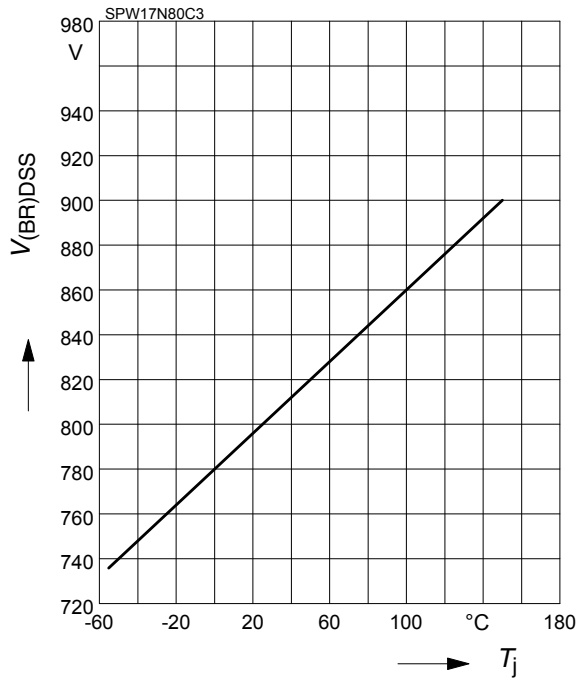
$$E_{AS} = f(T_j)$$

par.:  $I_D = 3.4\text{ A}, V_{DD} = 50\text{ V}$



**13 Drain-source breakdown voltage**

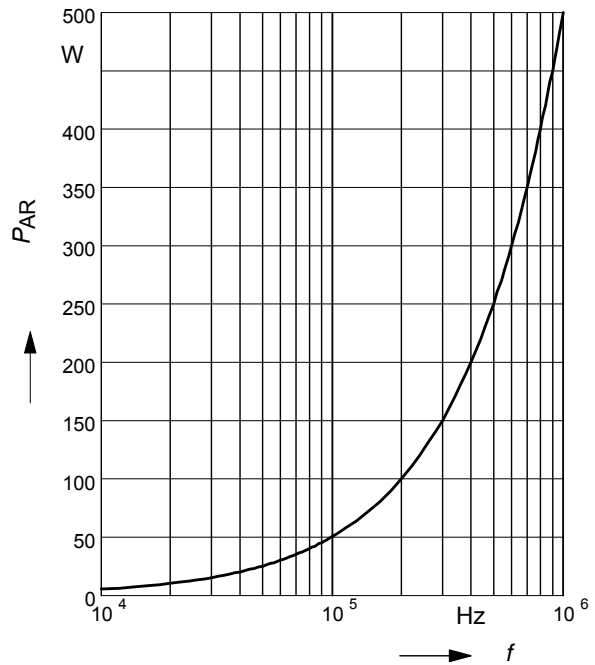
$$V_{(BR)DSS} = f(T_j)$$



**14 Avalanche power losses**

$$P_{AR} = f(f)$$

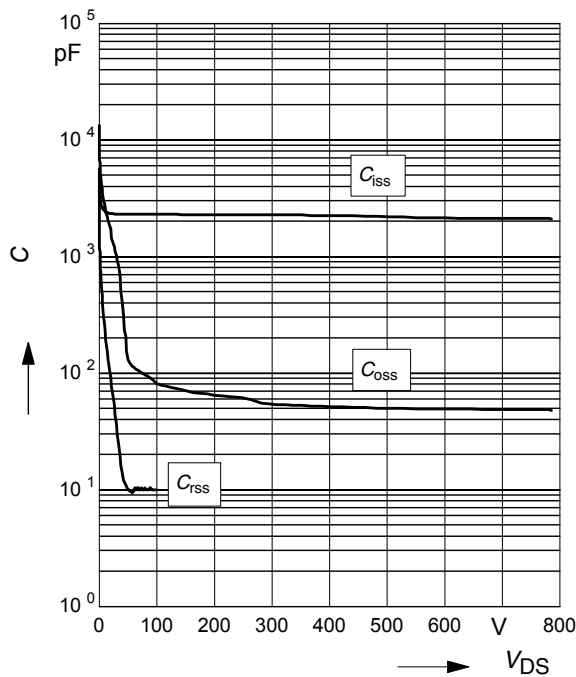
parameter:  $E_{AR}=0.5mJ$



**15 Typ. capacitances**

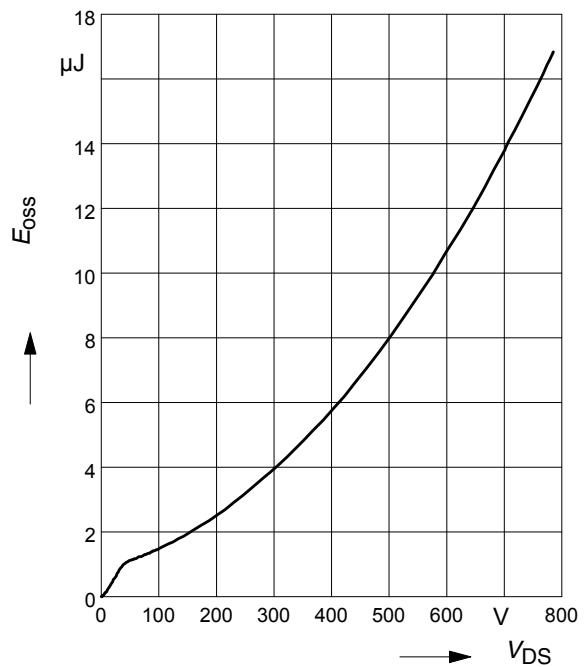
$$C = f(V_{DS})$$

parameter:  $V_{GS}=0V, f=1\text{ MHz}$



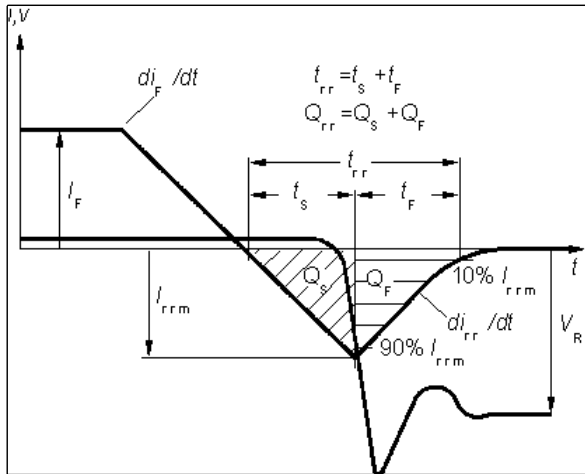
**16 Typ.  $C_{OSS}$  stored energy**

$$E_{OSS} = f(V_{DS})$$

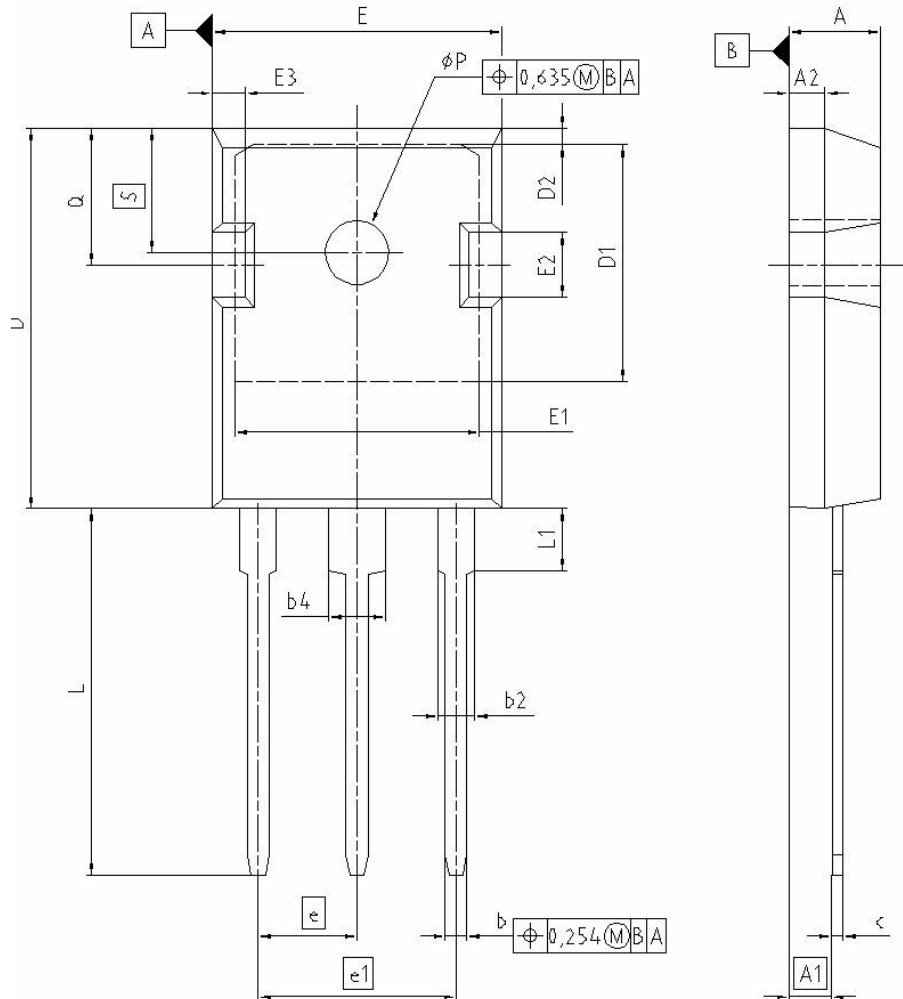




Definition of diodes switching characteristics



PG-TO-247-3-1



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.903	5.157	0.193	0.203
A1	2.273	2.527	0.092	0.096
A2	1.853	2.107	0.075	0.081
b	1.073	1.327	0.047	0.052
b2	1.903	2.386	0.075	0.094
b4	2.870	3.454	0.113	0.136
c	0.549	0.752	0.024	0.030
D	20.823	21.077	0.820	0.830
D1	17.323	17.831	0.682	0.702
D2	1.063	1.317	0.042	0.052
E	15.773	16.027	0.621	0.631
E1	13.893	14.147	0.547	0.557
E2	3.683	3.937	0.145	0.155
E3	1.683	1.937	0.066	0.076
e	5.450		0.215	
e1	10.900		0.430	
N	3		3	
L	20.053	20.307	0.789	0.799
L1	4.168	4.472	0.164	0.176
phi P	3.559	3.661	0.140	0.144
Q	5.493	5.747	0.216	0.226
S	6.043	6.297	0.238	0.248

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**SCALE**

**EUROPEAN PROJECTION**

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